# **ECH8695R**



http://onsemi.com

# N-Channel Power MOSFET 24V, 11A, 9.1mΩ, Dual ECH8 Common Drain

#### **Features**

- Low On-resistance
- 2.5V drive
- Common-drain type
- Protection diode in

- Built-in gate protection resistor
- Best suited for LiB charging and discharging switch
- Halogen free compliance

## **Specifications**

**Absolute Maximum Ratings** at Ta = 25°C

Parameter	Symbol	Conditions	Value	Unit
Drain to Source Voltage	V <sub>DSS</sub>		24	V
Gate to Source Voltage	VGSS		±12.5	V
Drain Current (DC)	ID		11	Α
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	60	Α
Power Dissipation	PD	When mounted on ceramic substrate(900mm <sup>2</sup> ×0.8mm) 1unit	1.4	W
Total Dissipation	PT	When mounted on ceramic substrate(900mm <sup>2</sup> ×0.8mm)	1.5	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		- 55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### **Thermal Resistance Ratings**

Parameter	Symbol	Value	Unit
Junction to Ambient	Po	89.3	°C /W
When mounted on ceramic substrate (900mm <sup>2</sup> ×0.8mm) 1unit	$R_{\theta JA}$	09.3	C /vv

### **Electrical Characteristics** at Ta = 25°C

Parameter	Symbol	Conditions	Value			
			min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V	24			٧
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V			1	μΑ
Gate to Source Leakage Current	IGSS	VGS=±8V, VDS=0V			±1	μΑ
Gate Threshold Voltage	VGS(th)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	0.5		1.3	٧
Forward Transconductance	gFS .	V <sub>DS</sub> =10V, I <sub>D</sub> =5A		6.5		S
Static Drain to Source On-State Resistance	R <sub>DS</sub> (on)1	I <sub>D</sub> =5A, V <sub>GS</sub> =4.5V	5.6	7.0	9.1	mΩ
	R <sub>DS</sub> (on)2	I <sub>D</sub> =5A, V <sub>GS</sub> =4.0V	5.8	7.3	9.5	mΩ
	R <sub>DS</sub> (on)3	I <sub>D</sub> =5A, V <sub>GS</sub> =3.1V	6.5	8.2	11.5	mΩ
	R <sub>DS</sub> (on)4	I <sub>D</sub> =2.5A, V <sub>GS</sub> =2.5V	7.6	9.5	13.3	mΩ

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#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 2 of this data sheet.

## **ECH8695R**

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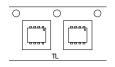
Parameter	Completel	Conditions	Value			11.7
	Symbol		min	typ	max	Unit
Turn-ON Delay Time	t <sub>d</sub> (on)	See specified Test Circuit.		300		ns
Rise Time	t <sub>r</sub>			320		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)			19700		ns
Fall Time	t <sub>f</sub>			22300		ns
Total Gate Charge	Qg	V <sub>DS</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =11A		10		nC
Gate to Source Charge	Qgs			1.6		nC
Gate to Drain "Miller" Charge	Qgd			1.5		nC
Forward Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> =11A, V <sub>GS</sub> =0V		0.77	1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

# **Ordering & Package Information**

Device	Package	Shipping	note
ECH8695R-TL-W	ECH8	3,000 pcs. / reel	Pb-Free and Halogen Free

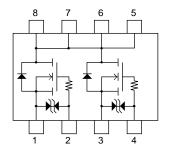
# Packing Type:TL



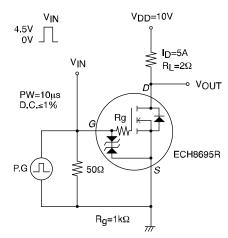
## Marking

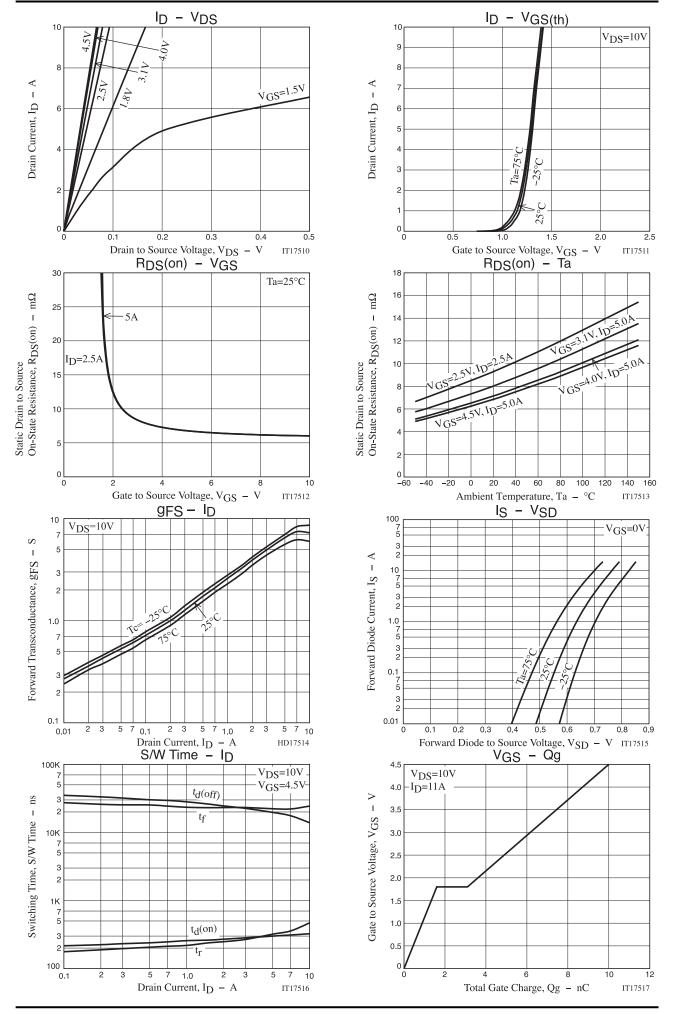


### **Electrical Connection**

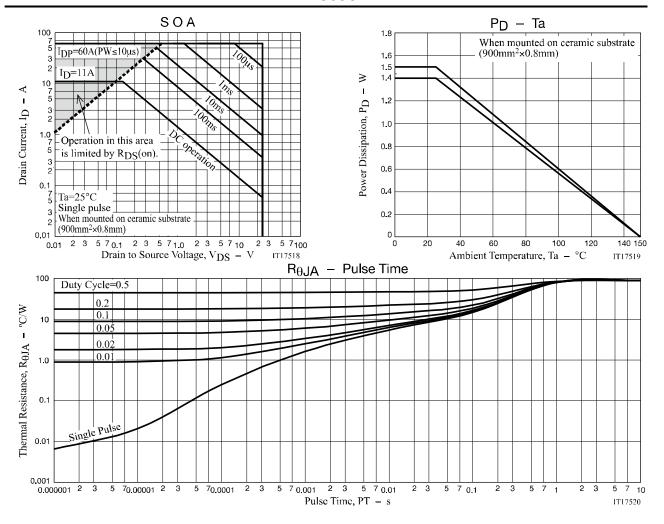


# **Switching Time Test Circuit**



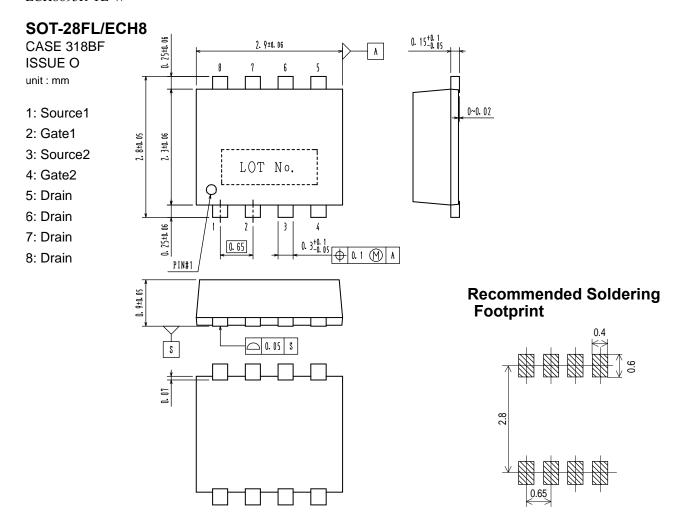


## **ECH8695R**



## **Package Dimensions**

ECH8695R-TL-W



Note on usage: Since the ECH8695R is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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